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(54) **VAPOR GROWTH APPARATUS**

(57) Abstract:

PURPOSE: To reduce a slip caused by thermal stress generated at a semiconductor substrate by forming the rear surface shape of a susceptor in a recess in which its outer periphery and its inner periphery are thick.

CONSTITUTION: A susceptor 1 supported at its center by an axial tube is so formed in a recess 1-3 that its front surface is smooth and its rear surface is thick at its outer periphery 1-1 and its inner periphery 1-2. A high frequency coil 3 is passed perpendicularly to a supporting plate 4, and partly supported to the upper ends of a plurality of supporting rods 5 adjustably provided in the heights of the upper ends. Thus, the rear surface of the susceptor is formed in the recess and the coil 3 is provided horizontally thereby to make the temperature distribution of a semiconductor substrate uniform at the time of temperature rise to reduce temperature difference. Thus, the dislocation of a slip of the crystal caused by a thermal stress can be reduced.

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